Discrete POWER & Signal **Technologies**

2N5306

FAIRCHILD SEMICONDUCTOR TM

2N5306



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	25	V
V_{EBO}	Emitter-Base Voltage 12		V
Ic	Collector Current - Continuous 1.2 A		A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted			
Symbol	Characteristic	Max	Units
		2N5306	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W

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		Test Conditions	Min	Max	Units
OFF CHAR	RACTERISTICS				
/ _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	25		V
/ _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 0.1 \ \mu {\rm A}, \ I_{\rm E} = 0$	25		V
/ _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 0.1 \mu A, I_{C} = 0$	12		V
СВО	Collector Cutoff Current	$V_{CB} = 25 \text{ V}, \text{ I}_{E} = 0$		0.1	μΑ
		$V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100 \text{ °C}$ $V_{EB} = 12 \text{ V}, I_C = 0$		20	μA
EBO	Emitter Cutoff Current	$V_{EB} = 12 V, I_{C} = 0$		0.1	μA
	ACTERISTICS*				
	DC Current Gain		7 000	70.000	r
η _{FE}	De current Gam	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ mA}$	7,000 20,000	70,000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 200 \text{ mA}, I_{\rm B} = 0.2 \text{ mA}$,	1.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 200 \text{ mA}, I_{\rm B} = 0.2 \text{ mA}$		1.6	V
V _{BE(on)}	Base-Emitter On Voltage	$I_{\rm C}$ = 200 mA, $V_{\rm CE}$ = 5.0 V		1.5	V
			-		
SMALL SIG	GNAL CHARACTERISTICS				
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		10	pF
λfe	Small-Signal Current Gain	$I_{\rm C} = 2.0 \text{ mA}, V_{\rm CE} = 5.0 \text{ V},$			
		f = 1.0 kHz I _c =2.0 mA, V _{CE} = 5.0 V,	7,000		
		f = 10 MHz	6.0		
*Dulas Testi F	Pulse Width ≤ 300 u.s. Duty Cvcle ≤ 2.0%				
Fuise Test. F	Fulse width \leq 500 µs, Duty Cycle \leq 2.0%				



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March 2001, Rev. B1





July 1999, Rev. A



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